BT139-800E



4Q Triac

Rev. 04 — 24 March 2011

Product data sheet

1. Product profile

1.1 General description

Planar passivated sensitive gate four quadrant triac in a SOT404 (D2PAK) surface-mountable plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

1.2 Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Triggering in all four quadrants

1.3 Applications

General purpose phase control

General purpose switching

1.4 Quick reference data

Table 1. Quick reference data

	44.1011.1010.1010					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	-	155	Α
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 99 ^{\circ}\text{C}$; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	-	16	Α
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{ Company of the company $	-	2.5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	-	4	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	-	5	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G+;} $ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	-	11	25	mA



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		N.I.
2	T2	main terminal 2	mb	T2—T1
3	G	gate		`G sym051
mb	T2	mounting base; main terminal 2	1 2 3	
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT139-800E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 99$ °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	16	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	155	Α
		full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms	-	170	Α
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	120	A^2s
dl _T /dt	rate of rise of on-state current	I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2+ G+	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2+ G-	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2- G-	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	2	Α
V_{GM}	peak gate voltage		-	5	V
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

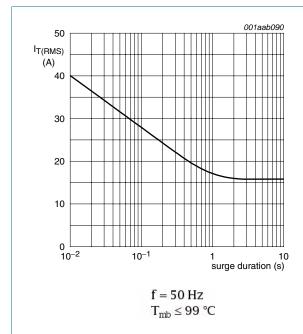


Fig 1. RMS on-state current as a function of surge duration; maximum values

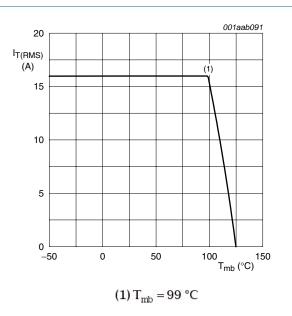


Fig 2. RMS on-state current as a function of mounting base temperature; maximum values

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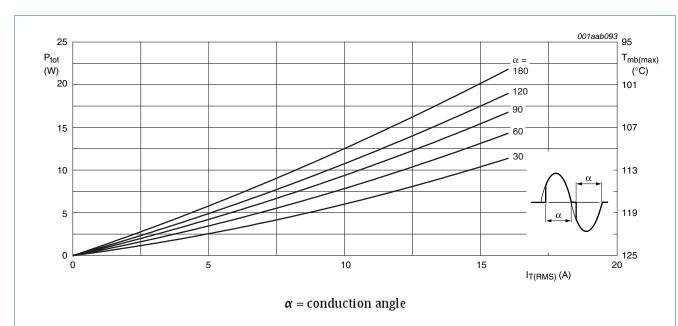


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values.

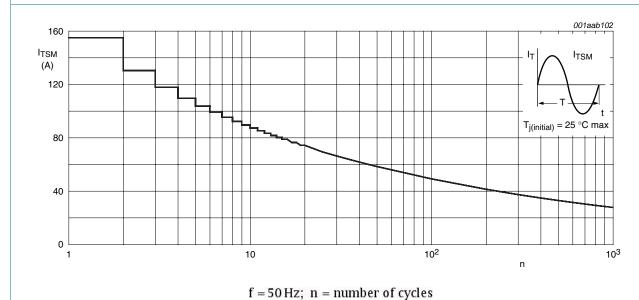
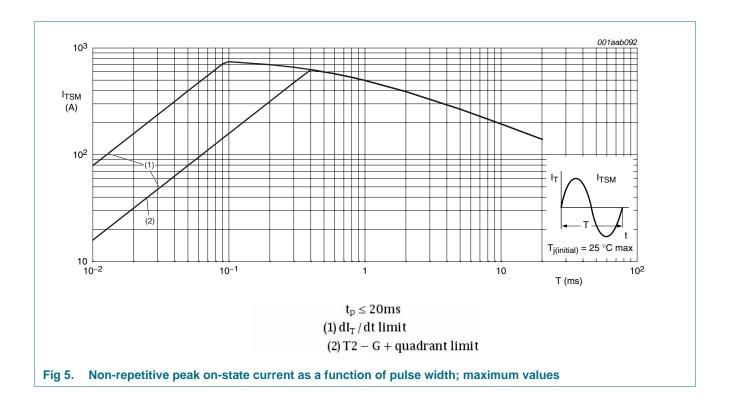


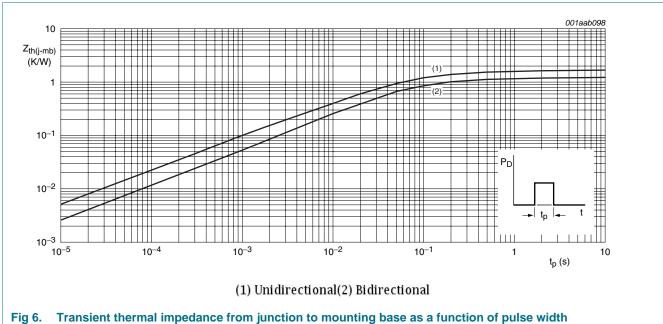
Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



Thermal characteristics

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to	half cycle; see Figure 6	-	-	1.7	K/W
	mounting base	full cycle; see Figure 6	-	-	1.2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



Transient thermal impedance from junction to mounting base as a function of pulse width

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
•	racteristics			,		
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{I}}$	-	2.5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{\text{ I}}$	-	4	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{\text{I}}$	-	5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{\text{I}}$	-	11	25	mA
I _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{\text{I}}$	-	3.2	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{\text{I}}$	-	16	40	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$	-	4	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$	-	5.5	40	mA
I _H	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{}$	-	4	45	mΑ
V _T	on-state voltage	$I_T = 20 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 10}}{\text{Figure 10}}$	-	1.2	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 11</u>	-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C};$ see <u>Figure 11</u>	0.25	0.4	-	V
I _D	off-state current	$V_D = 800 \text{ V}; T_j = 125 ^{\circ}\text{C}$	-	0.1	0.5	mΑ
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; exponential waveform; gate open circuit	-	50	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 20 A; V_D = 800 V; I_G = 0.1 A; dI_G/dt = 5 A/ μ s	-	2	-	μs

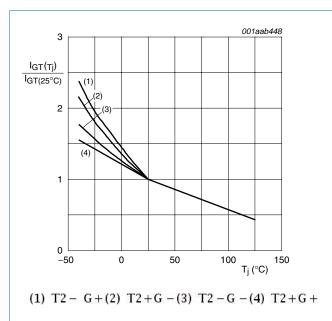


Fig 7. Normalized gate trigger current as a function of junction temperature

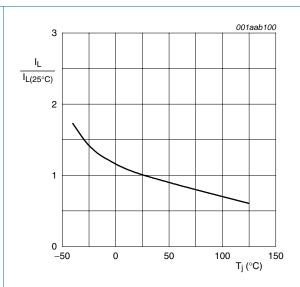


Fig 8. Normalized latching current as a function of junction temperature

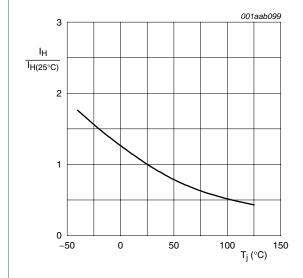
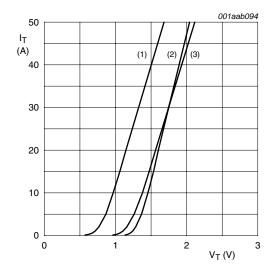


Fig 9. Normalized holding current as a function of junction temperature



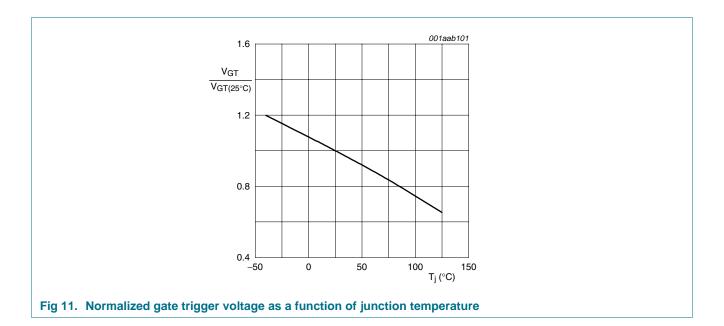
 $V_o = 1.195 \text{ V}$ $R_s = 0.018 \Omega$

(1) $T_j = 125$ °C; typical values

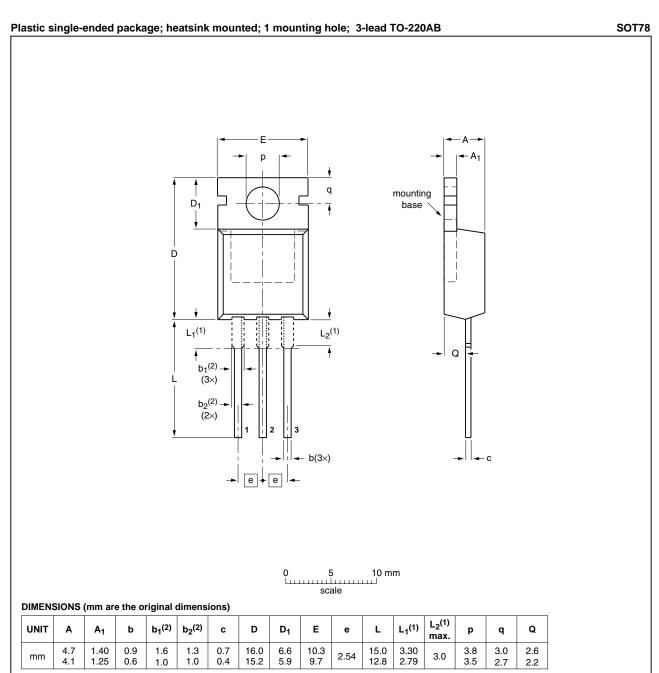
(2) $T_j = 25$ °C; maximum values

(3) $T_j = 125$ °C; maximum values

Fig 10. On-state current as a function of on-state voltage



7. Package outline



Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig 12. Package outline SOT78 (TO-220AB)

BT139-800E

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Revision history

Table 7. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BT139-800E v.4	20110324	Product data sheet	-	BT139_SER_E v.3		
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 					
	 Legal texts have been adapted to the new company name where appropriate. 					
	 Type number BT1: 	39-800E separated from o	data sheet BT139_SER_I	≣ v.3.		
BT139_SER_E v.3	20040923	Product data sheet	-	BT139_SERIES_E v.2		

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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